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### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Obsolete
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	40960
Number of I/O	186
Number of Gates	199000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	256-BGA
Supplier Device Package	256-FBGA (17x17)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/intel/ep1k50fc256-3aa">https://www.e-xfl.com/product-detail/intel/ep1k50fc256-3aa</a>

## Embedded Array Block

The EAB is a flexible block of RAM, with registers on the input and output ports, that is used to implement common gate array megafunctions. Because it is large and flexible, the EAB is suitable for functions such as multipliers, vector scalars, and error correction circuits. These functions can be combined in applications such as digital filters and microcontrollers.

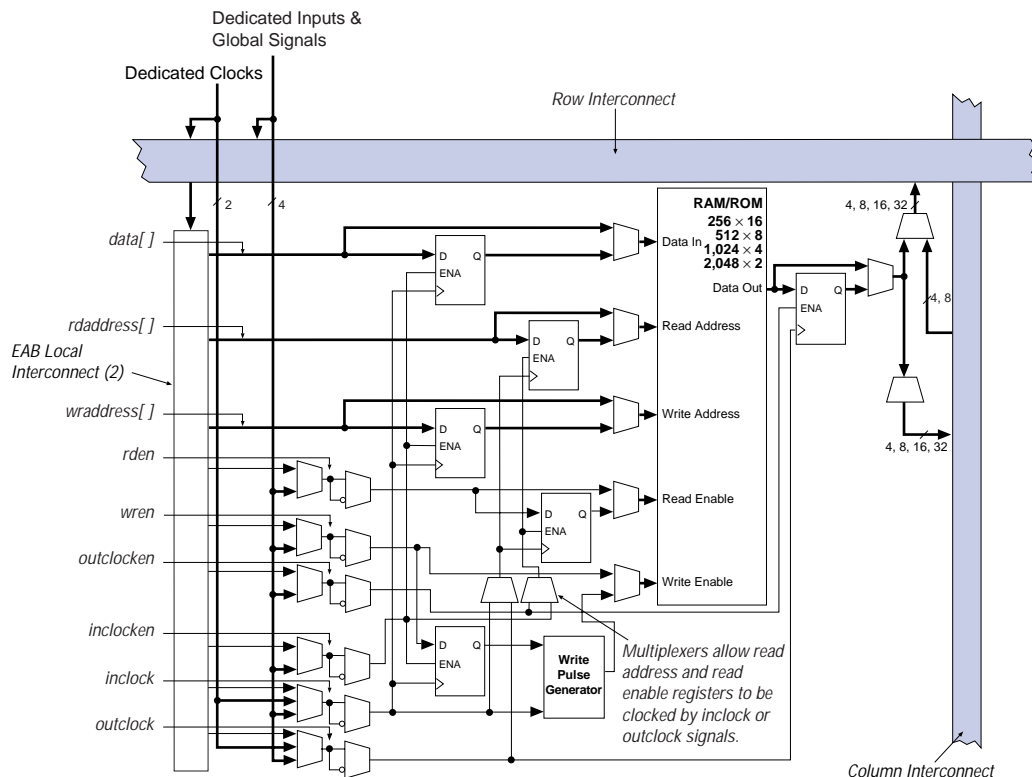
Logic functions are implemented by programming the EAB with a read-only pattern during configuration, thereby creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in a single logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement any function with 8 inputs and 16 outputs. Parameterized functions, such as LPM functions, can take advantage of the EAB automatically.

The ACEX 1K enhanced EAB supports dual-port RAM. The dual-port structure is ideal for FIFO buffers with one or two clocks. The ACEX 1K EAB can also support up to 16-bit-wide RAM blocks. The ACEX 1K EAB can act in dual-port or single-port mode. When in dual-port mode, separate clocks may be used for EAB read and write sections, allowing the EAB to be written and read at different rates. It also has separate synchronous clock enable signals for the EAB read and write sections, which allow independent control of these sections.

The EAB can also be used for bidirectional, dual-port memory applications where two ports read or write simultaneously. To implement this type of dual-port memory, two EABs are used to support two simultaneous reads or writes.

Alternatively, one clock and clock enable can be used to control the input registers of the EAB, while a different clock and clock enable control the output registers (see [Figure 2](#)).

Figure 2. ACEX 1K Device in Dual-Port RAM Mode *Note (1)*



**Notes:**

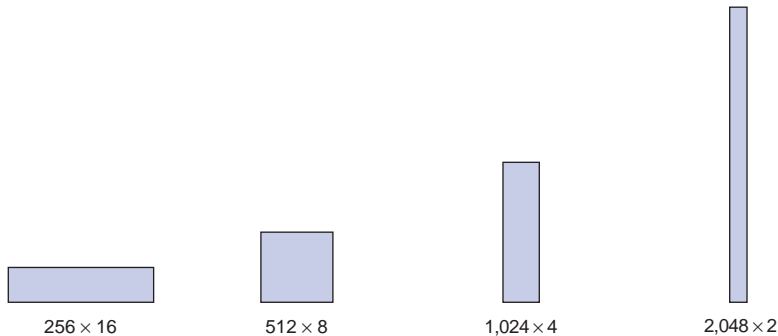
- (1) All registers can be asynchronously cleared by EAB local interconnect signals, global signals, or the chip-wide reset.
- (2) EP1K10, EP1K30, and EP1K50 devices have 88 EAB local interconnect channels; EP1K100 devices have 104 EAB local interconnect channels.

The EAB can use Altera megafunctions to implement dual-port RAM applications where both ports can read or write, as shown in Figure 3. The ACEX 1K EAB can also be used in a single-port mode (see Figure 4).

EABs can be used to implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the write enable signal. In contrast, the EAB's synchronous RAM generates its own write enable signal and is self-timed with respect to the input or write clock. A circuit using the EAB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

When used as RAM, each EAB can be configured in any of the following sizes:  $256 \times 16$ ;  $512 \times 8$ ;  $1,024 \times 4$ ; or  $2,048 \times 2$ . Figure 5 shows the ACEX 1K EAB memory configurations.

Figure 5. ACEX 1K EAB Memory Configurations



Larger blocks of RAM are created by combining multiple EABs. For example, two  $256 \times 16$  RAM blocks can be combined to form a  $256 \times 32$  block, and two  $512 \times 8$  RAM blocks can be combined to form a  $512 \times 16$  block. Figure 6 shows examples of multiple EAB combination.

Figure 6. Examples of Combining ACEX 1K EABs

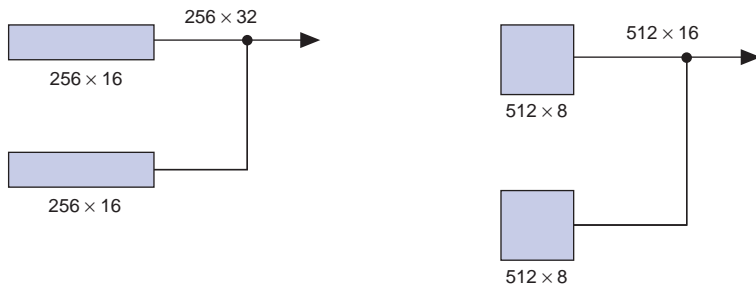
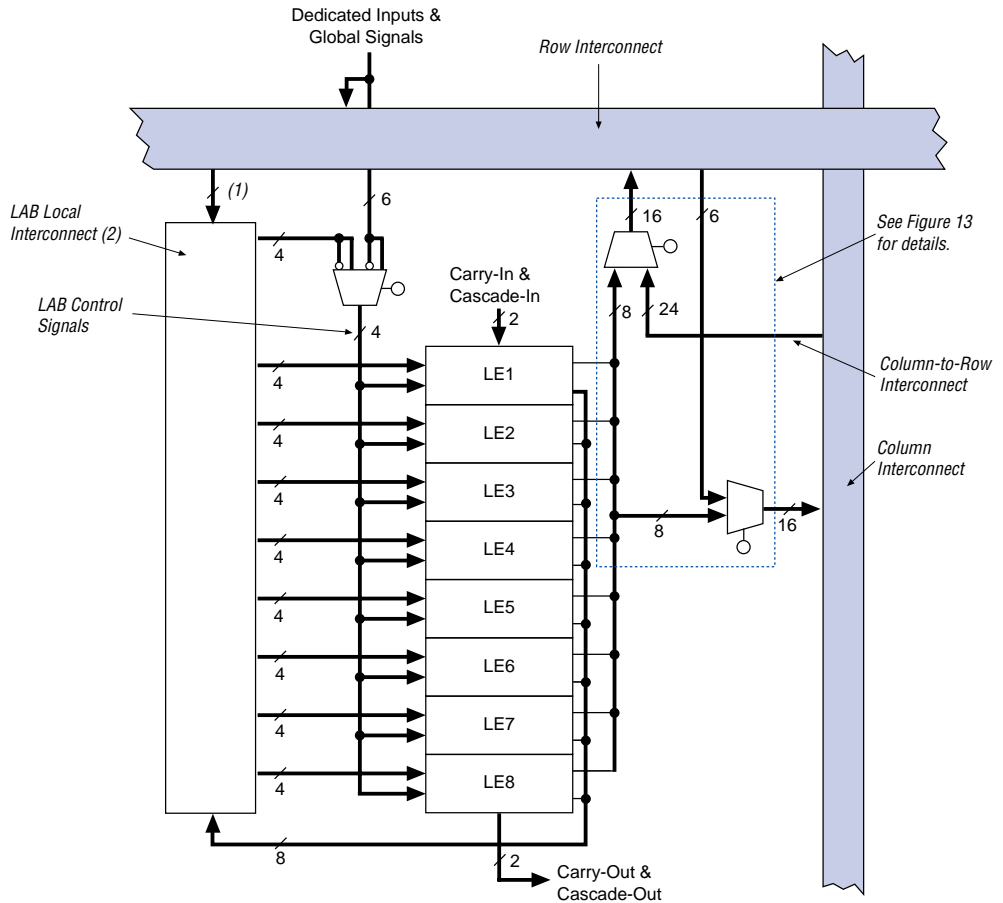


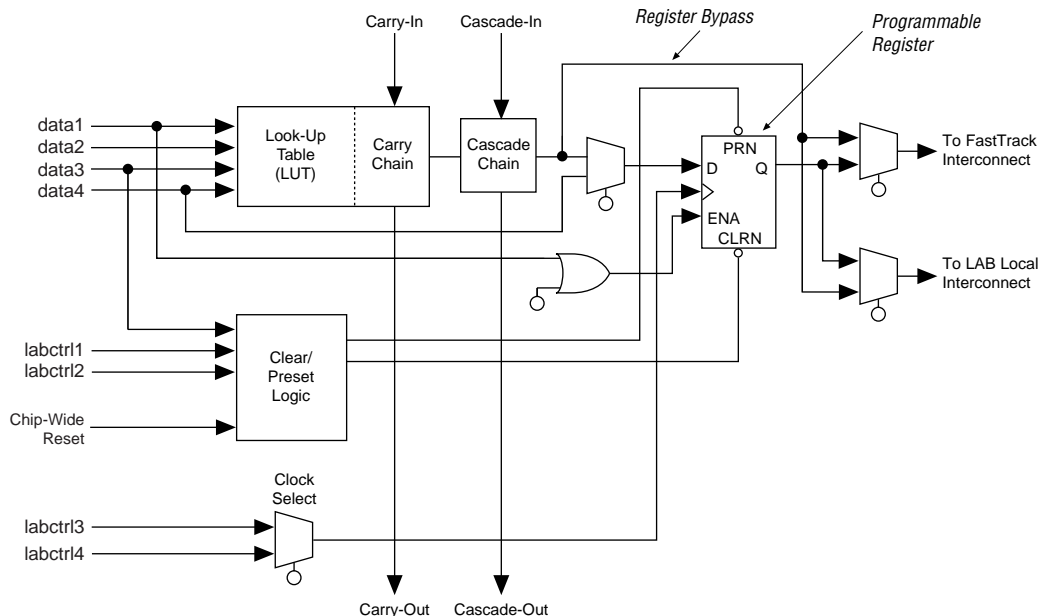
Figure 7. ACEX 1K LAB



**Notes:**

- (1) EP1K10, EP1K30, and EP1K50 devices have 22 inputs to the LAB local interconnect channel from the row; EP1K100 devices have 26.
- (2) EP1K10, EP1K30, and EP1K50 devices have 30 LAB local interconnect channels; EP1K100 devices have 34.

Figure 8. ACEX 1K Logic Element



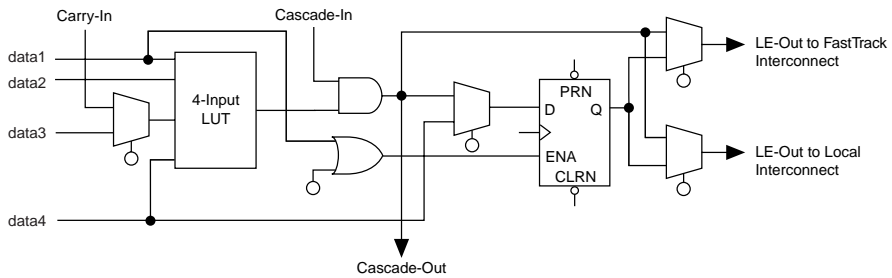
The programmable flipflop in the LE can be configured for D, T, JK, or SR operation. The clock, clear, and preset control signals on the flipflop can be driven by global signals, general-purpose I/O pins, or any internal logic. For combinational functions, the flipflop is bypassed and the LUT's output drives the LE's output.

The LE has two outputs that drive the interconnect: one drives the local interconnect, and the other drives either the row or column FastTrack Interconnect routing structure. The two outputs can be controlled independently. For example, the LUT can drive one output while the register drives the other output. This feature, called register packing, can improve LE utilization because the register and the LUT can be used for unrelated functions.

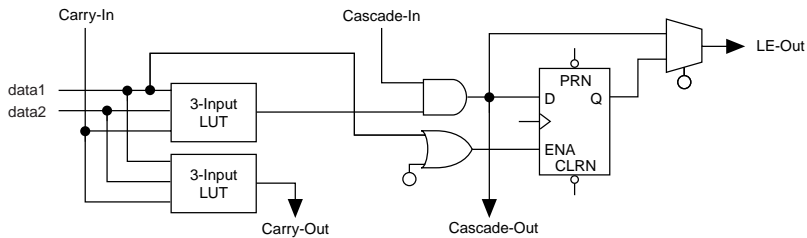
The ACEX 1K architecture provides two types of dedicated high-speed data paths that connect adjacent LEs without using local interconnect paths: carry chains and cascade chains. The carry chain supports high-speed counters and adders, and the cascade chain implements wide-input functions with minimum delay. Carry and cascade chains connect all LEs in a LAB and all LABs in the same row. Intensive use of carry and cascade chains can reduce routing flexibility. Therefore, the use of these chains should be limited to speed-critical portions of a design.

Figure 11. ACEX 1K LE Operating Modes

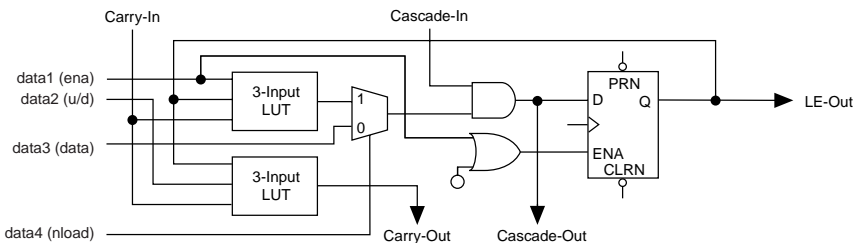
### Normal Mode



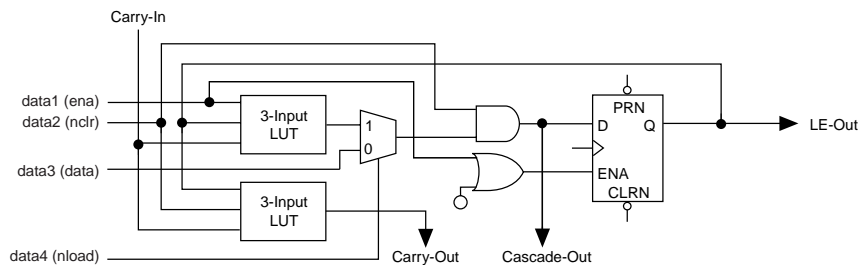
### Arithmetic Mode



### Up/Down Counter Mode



### Clearable Counter Mode



### Normal Mode

The normal mode is suitable for general logic applications and wide decoding functions that can take advantage of a cascade chain. In normal mode, four data inputs from the LAB local interconnect and the carry-in are inputs to a 4-input LUT. The compiler automatically selects the carry-in or the DATA3 signal as one of the inputs to the LUT. The LUT output can be combined with the cascade-in signal to form a cascade chain through the cascade-out signal. Either the register or the LUT can be used to drive both the local interconnect and the FastTrack Interconnect routing structure at the same time.

The LUT and the register in the LE can be used independently (register packing). To support register packing, the LE has two outputs; one drives the local interconnect, and the other drives the FastTrack Interconnect routing structure. The DATA4 signal can drive the register directly, allowing the LUT to compute a function that is independent of the registered signal; a 3-input function can be computed in the LUT, and a fourth independent signal can be registered. Alternatively, a 4-input function can be generated, and one of the inputs to this function can be used to drive the register. The register in a packed LE can still use the clock enable, clear, and preset signals in the LE. In a packed LE, the register can drive the FastTrack Interconnect routing structure while the LUT drives the local interconnect, or vice versa.

### Arithmetic Mode

The arithmetic mode offers two 3-input LUTs that are ideal for implementing adders, accumulators, and comparators. One LUT computes a 3-input function; the other generates a carry output. As shown in [Figure 11](#), the first LUT uses the carry-in signal and two data inputs from the LAB local interconnect to generate a combinatorial or registered output. For example, in an adder, this output is the sum of three signals: a, b, and carry-in. The second LUT uses the same three signals to generate a carry-out signal, thereby creating a carry chain. The arithmetic mode also supports simultaneous use of the cascade chain.

### Up/Down Counter Mode

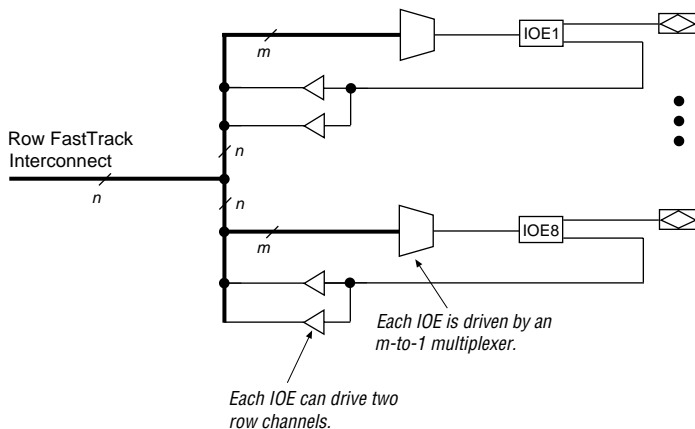
The up/down counter mode offers counter enable, clock enable, synchronous up/down control, and data loading options. These control signals are generated by the data inputs from the LAB local interconnect, the carry-in signal, and output feedback from the programmable register. Two 3-input LUTs are used; one generates the counter data, and the other generates the fast carry bit. A 2-to-1 multiplexer provides synchronous loading. Data can also be loaded asynchronously with the clear and preset register control signals without using the LUT resources.



### Row-to-IOE Connections

When an IOE is used as an input signal, it can drive two separate row channels. The signal is accessible by all LEs within that row. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the row channels. Up to eight IOEs connect to each side of each row channel (see Figure 16).

Figure 16. ACEX 1K Row-to-IOE Connections *Note (1)*



**Note:**

(1) The values for  $m$  and  $n$  are shown in Table 8.

Table 8 lists the ACEX 1K row-to-IOE interconnect resources.

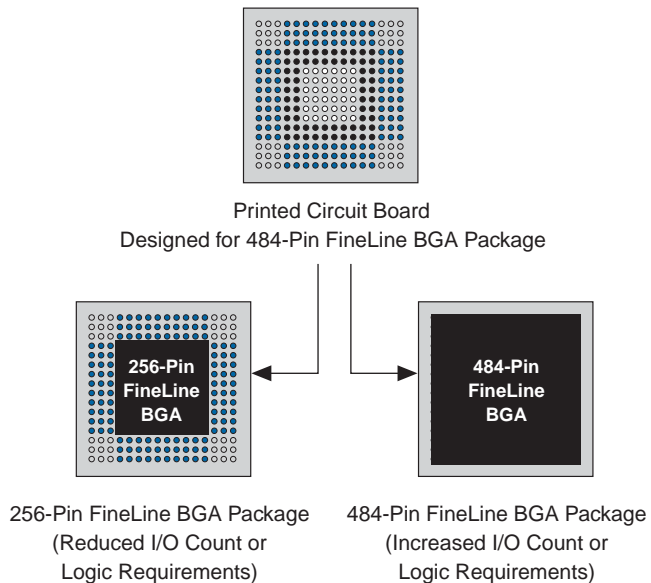
Table 8. ACEX 1K Row-to-IOE Interconnect Resources		
Device	Channels per Row ( $n$ )	Row Channels per Pin ( $m$ )
EP1K10	144	18
EP1K30	216	27
EP1K50	216	27
EP1K100	312	39

## SameFrame Pin-Outs

ACEX 1K devices support the SameFrame pin-out feature for FineLine BGA packages. The SameFrame pin-out feature is the arrangement of balls on FineLine BGA packages such that the lower-ball-count packages form a subset of the higher-ball-count packages. SameFrame pin-outs provide the flexibility to migrate not only from device to device within the same package, but also from one package to another. A given printed circuit board (PCB) layout can support multiple device density/package combinations. For example, a single board layout can support a range of devices from an EP1K10 device in a 256-pin FineLine BGA package to an EP1K100 device in a 484-pin FineLine BGA package.

The Altera software provides support to design PCBs with SameFrame pin-out devices. Devices can be defined for present and future use. The Altera software generates pin-outs describing how to lay out a board that takes advantage of this migration. [Figure 18](#) shows an example of SameFrame pin-out.

*Figure 18. SameFrame Pin-Out Example*



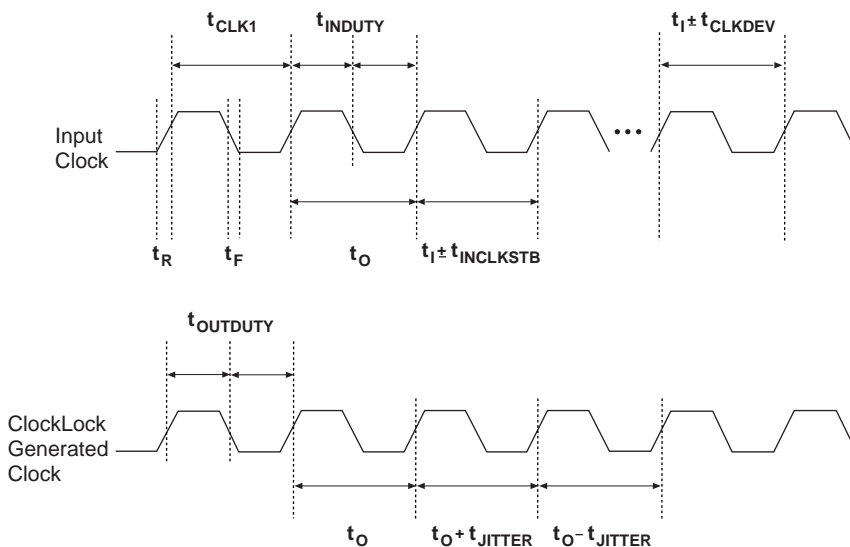
[Table 10](#) shows the ACEX 1K device/package combinations that support SameFrame pin-outs for ACEX 1K devices. All FineLine BGA packages support SameFrame pin-outs, providing the flexibility to migrate not only from device to device within the same package, but also from one package to another. The I/O count will vary from device to device.

For designs that require both a multiplied and non-multiplied clock, the clock trace on the board can be connected to the GCLK1 pin. In the Altera software, the GCLK1 pin can feed both the ClockLock and ClockBoost circuitry in the ACEX 1K device. However, when both circuits are used, the other clock pin cannot be used.

### ClockLock & ClockBoost Timing Parameters

For the ClockLock and ClockBoost circuitry to function properly, the incoming clock must meet certain requirements. If these specifications are not met, the circuitry may not lock onto the incoming clock, which generates an erroneous clock within the device. The clock generated by the ClockLock and ClockBoost circuitry must also meet certain specifications. If the incoming clock meets these requirements during configuration, the ClockLock and ClockBoost circuitry will lock onto the clock during configuration. The circuit will be ready for use immediately after configuration. Figure 19 shows the incoming and generated clock specifications.

Figure 19. Specifications for the Incoming & Generated Clocks *Note (1)*



**Note:**

- (1) The  $t_I$  parameter refers to the nominal input clock period; the  $t_O$  parameter refers to the nominal output clock period.

The  $V_{CCINT}$  pins must always be connected to a 2.5-V power supply. With a 2.5-V  $V_{CCINT}$  level, input voltages are compatible with 2.5-V, 3.3-V, and 5.0-V inputs. The  $V_{CCIO}$  pins can be connected to either a 2.5-V or 3.3-V power supply, depending on the output requirements. When the  $V_{CCIO}$  pins are connected to a 2.5-V power supply, the output levels are compatible with 2.5-V systems. When the  $V_{CCIO}$  pins are connected to a 3.3-V power supply, the output high is at 3.3 V and is therefore compatible with 3.3-V or 5.0-V systems. Devices operating with  $V_{CCIO}$  levels higher than 3.0 V achieve a faster timing delay of  $t_{OD2}$  instead of  $t_{OD1}$ .

**Table 13** summarizes ACEX 1K MultiVolt I/O support.

<i>Table 13. ACEX 1K MultiVolt I/O Support</i>						
$V_{CCIO}$ (V)	Input Signal (V)			Output Signal (V)		
	2.5	3.3	5.0	2.5	3.3	5.0
2.5	✓	✓ (1)	✓ (1)	✓		
3.3	✓	✓	✓ (1)	✓ (2)	✓	✓

**Notes:**

- (1) The PCI clamping diode must be disabled on an input which is driven with a voltage higher than  $V_{CCIO}$ .
- (2) When  $V_{CCIO} = 3.3$  V, an ACEX 1K device can drive a 2.5-V device that has 3.3-V tolerant inputs.

Open-drain output pins on ACEX 1K devices (with a pull-up resistor to the 5.0-V supply) can drive 5.0-V CMOS input pins that require a higher  $V_{IH}$  than LVTTL. When the open-drain pin is active, it will drive low. When the pin is inactive, the resistor will pull up the trace to 5.0 V, thereby meeting the CMOS  $V_{OH}$  requirement. The open-drain pin will only drive low or tri-state; it will never drive high. The rise time is dependent on the value of the pull-up resistor and load impedance. The  $I_{OL}$  current specification should be considered when selecting a pull-up resistor.

## Power Sequencing & Hot-Socketing

Because ACEX 1K devices can be used in a mixed-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. The  $V_{CCIO}$  and  $V_{CCINT}$  power planes can be powered in any order.

Signals can be driven into ACEX 1K devices before and during power up without damaging the device. Additionally, ACEX 1K devices do not drive out during power up. Once operating conditions are reached, ACEX 1K devices operate as specified by the user.

Table 19. ACEX 1K Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CCINT</sub>	Supply voltage for internal logic and input buffers	(3), (4)	2.375 (2.375)	2.625 (2.625)	V
V <sub>CCIO</sub>	Supply voltage for output buffers, 3.3-V operation	(3), (4)	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	(3), (4)	2.375 (2.375)	2.625 (2.625)	V
V <sub>I</sub>	Input voltage	(2), (5)	−0.5	5.75	V
V <sub>O</sub>	Output voltage		0	V <sub>CCIO</sub>	V
T <sub>A</sub>	Ambient temperature	Commercial range	0	70	°C
		Industrial range	−40	85	°C
T <sub>J</sub>	Junction temperature	Commercial range	0	85	°C
		Industrial range	−40	100	°C
		Extended range	−40	125	°C
t <sub>R</sub>	Input rise time			40	ns
t <sub>F</sub>	Input fall time			40	ns

Table 20. ACEX 1K Device DC Operating Conditions (Part 1 of 2) Notes (6), (7)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>IH</sub>	High-level input voltage		1.7, 0.5 × V <sub>CCIO</sub> (8)		5.75	V
V <sub>IL</sub>	Low-level input voltage		−0.5		0.8, 0.3 × V <sub>CCIO</sub> (8)	V
V <sub>OH</sub>	3.3-V high-level TTL output voltage	I <sub>OH</sub> = −8 mA DC, V <sub>CCIO</sub> = 3.00 V (9)	2.4			V
	3.3-V high-level CMOS output voltage	I <sub>OH</sub> = −0.1 mA DC, V <sub>CCIO</sub> = 3.00 V (9)	V <sub>CCIO</sub> − 0.2			V
	3.3-V high-level PCI output voltage	I <sub>OH</sub> = −0.5 mA DC, V <sub>CCIO</sub> = 3.00 to 3.60 V (9)	0.9 × V <sub>CCIO</sub>			V
	2.5-V high-level output voltage	I <sub>OH</sub> = −0.1 mA DC, V <sub>CCIO</sub> = 2.375 V (9)	2.1			V
		I <sub>OH</sub> = −1 mA DC, V <sub>CCIO</sub> = 2.375 V (9)	2.0			V
		I <sub>OH</sub> = −2 mA DC, V <sub>CCIO</sub> = 2.375 V (9)	1.7			V

Table 21. ACEX 1K Device Capacitance *Note (14)*

Symbol	Parameter	Conditions	Min	Max	Unit
$C_{IN}$	Input capacitance	$V_{IN} = 0\text{ V}$ , $f = 1.0\text{ MHz}$		10	pF
$C_{INCLK}$	Input capacitance on dedicated clock pin	$V_{IN} = 0\text{ V}$ , $f = 1.0\text{ MHz}$		12	pF
$C_{OUT}$	Output capacitance	$V_{OUT} = 0\text{ V}$ , $f = 1.0\text{ MHz}$		10	pF

**Notes to tables:**

- (1) See the *Operating Requirements for Altera Devices Data Sheet*.
- (2) Minimum DC input voltage is  $-0.5\text{ V}$ . During transitions, the inputs may undershoot to  $-2.0\text{ V}$  for input currents less than  $100\text{ mA}$  and periods shorter than  $20\text{ ns}$ .
- (3) Numbers in parentheses are for industrial- and extended-temperature-range devices.
- (4) Maximum  $V_{CC}$  rise time is  $100\text{ ms}$ , and  $V_{CC}$  must rise monotonically.
- (5) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before  $V_{CCINT}$  and  $V_{CCIO}$  are powered.
- (6) Typical values are for  $T_A = 25^\circ\text{ C}$ ,  $V_{CCINT} = 2.5\text{ V}$ , and  $V_{CCIO} = 2.5\text{ V}$  or  $3.3\text{ V}$ .
- (7) These values are specified under the ACEX 1K Recommended Operating Conditions shown in Table 19 on page 46.
- (8) The ACEX 1K input buffers are compatible with  $2.5\text{-V}$ ,  $3.3\text{-V}$  (LVTTTL and LVCMOS), and  $5.0\text{-V}$  TTL and CMOS signals. Additionally, the input buffers are  $3.3\text{-V}$  PCI compliant when  $V_{CCIO}$  and  $V_{CCINT}$  meet the relationship shown in Figure 22.
- (9) The  $I_{OH}$  parameter refers to high-level TTL, PCI, or CMOS output current.
- (10) The  $I_{OL}$  parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
- (11) This value is specified for normal device operation. The value may vary during power-up.
- (12) This parameter applies to -1 speed grade commercial temperature devices and -2 speed grade industrial and extended temperature devices.
- (13) Pin pull-up resistance values will be lower if the pin is driven higher than  $V_{CCIO}$  by an external source.
- (14) Capacitance is sample-tested only.

Table 39. EP1K30 Device EAB Internal Microparameters *Note (1)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.7		2.0		2.3	ns
$t_{EABDATA1}$		0.6		0.7		0.8	ns
$t_{EABWE1}$		1.1		1.3		1.4	ns
$t_{EABWE2}$		0.4		0.4		0.5	ns
$t_{EABRE1}$		0.8		0.9		1.0	ns
$t_{EABRE2}$		0.4		0.4		0.5	ns
$t_{EABCLK}$		0.0		0.0		0.0	ns
$t_{EABCO}$		0.3		0.3		0.4	ns
$t_{EABYPASS}$		0.5		0.6		0.7	ns
$t_{EABSU}$	0.9		1.0		1.2		ns
$t_{EABH}$	0.4		0.4		0.5		ns
$t_{EABCLR}$	0.3		0.3		0.3		ns
$t_{AA}$		3.2		3.8		4.4	ns
$t_{WP}$	2.5		2.9		3.3		ns
$t_{RP}$	0.9		1.1		1.2		ns
$t_{WDSU}$	0.9		1.0		1.1		ns
$t_{WDH}$	0.1		0.1		0.1		ns
$t_{WASU}$	1.7		2.0		2.3		ns
$t_{WAH}$	1.8		2.1		2.4		ns
$t_{RASU}$	3.1		3.7		4.2		ns
$t_{RAH}$	0.2		0.2		0.2		ns
$t_{WO}$		2.5		2.9		3.3	ns
$t_{DD}$		2.5		2.9		3.3	ns
$t_{EABOUT}$		0.5		0.6		0.7	ns
$t_{EABCH}$	1.5		2.0		2.3		ns
$t_{EABCL}$	2.5		2.9		3.3		ns

Table 40. EP1K30 Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
$t_{EABAA}$		6.4		7.6		8.8	ns
$t_{EABRCOMB}$	6.4		7.6		8.8		ns
$t_{EABRCREG}$	4.4		5.1		6.0		ns
$t_{EABWP}$	2.5		2.9		3.3		ns
$t_{EABWCOMB}$	6.0		7.0		8.0		ns
$t_{EABWCREG}$	6.8		7.8		9.0		ns
$t_{EABDD}$		5.7		6.7		7.7	ns
$t_{EABDATA CO}$		0.8		0.9		1.1	ns
$t_{EABDATASU}$	1.5		1.7		2.0		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	1.3		1.4		1.7		ns
$t_{EABWEH}$	0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.5		1.7		2.0		ns
$t_{EABWDH}$	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.0		3.6		4.3		ns
$t_{EABWAH}$	0.5		0.5		0.4		ns
$t_{EABWO}$		5.1		6.0		6.8	ns



Table 41. EP1K30 Device Interconnect Timing Microparameters *Note (1)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		1.8		2.4		2.9	ns
$t_{DIN2LE}$		1.5		1.8		2.4	ns
$t_{DIN2DATA}$		1.5		1.8		2.2	ns
$t_{DCLK2IOE}$		2.2		2.6		3.0	ns
$t_{DCLK2LE}$		1.5		1.8		2.4	ns
$t_{SAMELAB}$		0.1		0.2		0.3	ns
$t_{SAMEROW}$		2.0		2.4		2.7	ns
$t_{SAMECOLUMN}$		0.7		1.0		0.8	ns
$t_{DIFFROW}$		2.7		3.4		3.5	ns
$t_{TWOROWS}$		4.7		5.8		6.2	ns
$t_{LEPERIPH}$		2.7		3.4		3.8	ns
$t_{LABCARRY}$		0.3		0.4		0.5	ns
$t_{LABCASC}$		0.8		0.8		1.1	ns

Table 42. EP1K30 External Timing Parameters *Notes (1), (2)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
t <sub>DDR</sub>		8.0		9.5		12.5	ns
t <sub>INSU</sub> (3)	2.1		2.5		3.9		ns
t <sub>INH</sub> (3)	0.0		0.0		0.0		ns
t <sub>OUTCO</sub> (3)	2.0	4.9	2.0	5.9	2.0	7.6	ns
t <sub>INSU</sub> (4)	1.1		1.5		–		ns
t <sub>INH</sub> (4)	0.0		0.0		–		ns
t <sub>OUTCO</sub> (4)	0.5	3.9	0.5	4.9	–	–	ns
t <sub>PCISU</sub>	3.0		4.2		–		ns
t <sub>PCIH</sub>	0.0		0.0		–		ns
t <sub>PCICO</sub>	2.0	6.0	2.0	7.5	–	–	ns

Table 43. EP1K30 External Bidirectional Timing Parameters *Notes (1), (2)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
t <sub>INSUBIDIR</sub> (3)	2.8		3.9		5.2		ns
t <sub>INHBIDIR</sub> (3)	0.0		0.0		0.0		ns
t <sub>INSUBIDIR</sub> (4)	3.8		4.9		–		ns
t <sub>INHBIDIR</sub> (4)	0.0		0.0		–		ns
t <sub>OUTCOBIDIR</sub> (3)	2.0	4.9	2.0	5.9	2.0	7.6	ns
t <sub>XZBIDIR</sub> (3)		6.1		7.5		9.7	ns
t <sub>ZXBIDIR</sub> (3)		6.1		7.5		9.7	ns
t <sub>OUTCOBIDIR</sub> (4)	0.5	3.9	0.5	4.9	–	–	ns
t <sub>XZBIDIR</sub> (4)		5.1		6.5		–	ns
t <sub>ZXBIDIR</sub> (4)		5.1		6.5		–	ns

**Notes to tables:**

- (1) All timing parameters are described in Tables 22 through 29 in this data sheet.
- (2) These parameters are specified by characterization.
- (3) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
- (4) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Tables 44 through 50 show EP1K50 device external timing parameters.

Table 44. EP1K50 Device LE Timing Microparameters (Part 1 of 2) *Note (1)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
$t_{LUT}$		0.6		0.8		1.1	ns
$t_{CLUT}$		0.5		0.6		0.8	ns
$t_{RLUT}$		0.6		0.7		0.9	ns
$t_{PACKED}$		0.2		0.3		0.4	ns
$t_{EN}$		0.6		0.7		0.9	ns
$t_{CICO}$		0.1		0.1		0.1	ns
$t_{CGEN}$		0.4		0.5		0.6	ns
$t_{CGENR}$		0.1		0.1		0.1	ns
$t_{CASC}$		0.5		0.8		1.0	ns
$t_C$		0.5		0.6		0.8	ns

Table 47. EP1K50 Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
$t_{EABAA}$		3.7		5.2		7.0	ns
$t_{EABRCCOMB}$	3.7		5.2		7.0		ns
$t_{EABRCREG}$	3.5		4.9		6.6		ns
$t_{EABWP}$	2.0		2.8		3.8		ns
$t_{EABWCCOMB}$	4.5		6.3		8.6		ns
$t_{EABWCREG}$	5.6		7.8		10.6		ns
$t_{EABDD}$		3.8		5.3		7.2	ns
$t_{EABDATA CO}$		0.8		1.1		1.5	ns
$t_{EABDATASU}$	1.1		1.6		2.1		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	0.7		1.0		1.3		ns
$t_{EABWEH}$	0.4		0.6		0.8		ns
$t_{EABWDSU}$	1.2		1.7		2.2		ns
$t_{EABWDH}$	0.0		0.0		0.0		ns
$t_{EABWASU}$	1.6		2.3		3.0		ns
$t_{EABWAH}$	0.9		1.2		1.8		ns
$t_{EABWO}$		3.1		4.3		5.9	ns

Table 48. EP1K50 Device Interconnect Timing Microparameters *Note (1)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		3.1		3.7		4.6	ns
$t_{DIN2LE}$		1.7		2.1		2.7	ns
$t_{DIN2DATA}$		2.7		3.1		5.1	ns
$t_{DCLK2IOE}$		1.6		1.9		2.6	ns
$t_{DCLK2LE}$		1.7		2.1		2.7	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		1.5		1.7		2.4	ns
$t_{SAMECOLUMN}$		1.0		1.3		2.1	ns
$t_{DIFFROW}$		2.5		3.0		4.5	ns
$t_{TROWROWS}$		4.0		4.7		6.9	ns
$t_{LEPERIPH}$		2.6		2.9		3.4	ns
$t_{LABCARRY}$		0.1		0.2		0.2	ns
$t_{LABCASC}$		0.8		1.0		1.3	ns

Table 49. EP1K50 External Timing Parameters *Note (1)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
t <sub>DDR</sub>		8.0		9.5		12.5	ns
t <sub>INSU</sub> (2)	2.4		2.9		3.9		ns
t <sub>INH</sub> (2)	0.0		0.0		0.0		ns
t <sub>OUTCO</sub> (2)	2.0	4.3	2.0	5.2	2.0	7.3	ns
t <sub>INSU</sub> (3)	2.4		2.9		–		ns
t <sub>INH</sub> (3)	0.0		0.0		–		ns
t <sub>OUTCO</sub> (3)	0.5	3.3	0.5	4.1	–	–	ns
t <sub>PCISU</sub>	2.4		2.9		–		ns
t <sub>PCIH</sub>	0.0		0.0		–		ns
t <sub>PCICO</sub>	2.0	6.0	2.0	7.7	–	–	ns

Table 55. EP1K100 Device Interconnect Timing Microparameters *Note (1)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		3.1		3.6		4.4	ns
$t_{DIN2LE}$		0.3		0.4		0.5	ns
$t_{DIN2DATA}$		1.6		1.8		2.0	ns
$t_{DCLK2IOE}$		0.8		1.1		1.4	ns
$t_{DCLK2LE}$		0.3		0.4		0.5	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		1.5		2.5		3.4	ns
$t_{SAMECOLUMN}$		0.4		1.0		1.6	ns
$t_{DIFFROW}$		1.9		3.5		5.0	ns
$t_{TWOROWS}$		3.4		6.0		8.4	ns
$t_{LEPERIPH}$		4.3		5.4		6.5	ns
$t_{LABCARRY}$		0.5		0.7		0.9	ns
$t_{LABCASC}$		0.8		1.0		1.4	ns

Table 56. EP1K100 External Timing Parameters *Notes (1), (2)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
t <sub>DDR</sub>		9.0		12.0		16.0	ns
t <sub>INSU</sub> (3)	2.0		2.5		3.3		ns
t <sub>INH</sub> (3)	0.0		0.0		0.0		ns
t <sub>OUTCO</sub> (3)	2.0	5.2	2.0	6.9	2.0	9.1	ns
t <sub>INSU</sub> (4)	2.0		2.2		—		ns
t <sub>INH</sub> (4)	0.0		0.0		—		ns
t <sub>OUTCO</sub> (4)	0.5	3.0	0.5	4.6	—	—	ns
t <sub>PCISU</sub>	3.0		6.2		—		ns
t <sub>PCIH</sub>	0.0		0.0		—		ns
t <sub>PCICO</sub>	2.0	6.0	2.0	6.9	—	—	ns